MSKSEMI















ESD

TVS

TSS

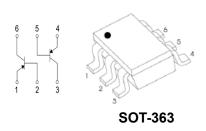
MOV

GDT

PLED

Broduct data sheet





BC857S

DUAL TRANSISTOR (PNP+PNP) Isolated Transistor and Diode

FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING: 3F MAXIMUM RATINGS(T_a=25°C unless otherwise noted)

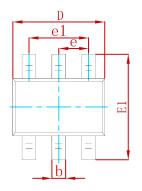
Symbol	Parameter	Value	Units
V _{CBO}	Collector- Base Voltage	-50	٧
V _{CEO}	Collector-Emitter Voltage	-45	٧
V _{EBO}	Emitter-Base Voltage	-5	٧
Ic	Collector Current -Continuous	-0.2	Α
Pc	Collector Power Dissipation	0.3	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	417	°C/W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature	-55-150	$^{\circ}$

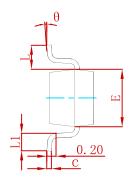
ELECTRICAL CHARACTERISTICS(Ta=25°C unless otherwise specified)

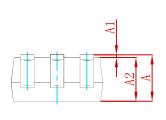
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	Ic=-10μA,I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	Ic=-10mA,I _B =0	-45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA,I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V,I _E =0			-15	nA
DC current gain	h _{FE}	V _{CE} =-5V,I _C =-2mA	125		630	
Collector emitter acturation valters	V _{CE(sat)(1)}	I _C =-10mA,I _B =-0.5mA			-0.3	V
Collector-emitter saturation voltage	V _{CE(sat)(2)}	I _C =-100mA,I _B =-5mA			-0.65	V
Page emitter voltage	V _{BE(1)}	V_{CE} =-5 V , I_{C} =-2 m A	-0.6		-0.75	V
Base-emitter voltage	V _{BE(2)}	V _{CE} =-5V,I _C =-10mA			-0.82	٧
Transition frequency	f _T	V _{CE} =-5V,I _C =-10mA,f=100MHz		200		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _E =0,f=1MHz		3.5		pF
Noise figure	NF	V_{CE} =-5V, I_c =-0.2mA, f=1kHZ,Rs=2K Ω ,BW=200Hz		2.5		dB



PACKAGE MECHANICAL DATA

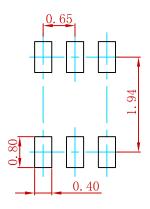






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
С	0.100	0.150	0.004	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.400	0.085	0.094	
е	0.650) TYP	0.026	S TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021	REF	
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters. 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BC857S	SOT-363	3000



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